RF Amplifier Data Sheet



BT01000-AlphaA 0.01MHz-3MHz 1kW

 Scientific and Industrial Applications



The BT-AlphaA series is a range of class AB RF power amplifiers covering the 10kHz to 3MHz frequency range.

- Rugged, solid-state design high reliability
- Extremely high phase and amplitude stability
- Very fast pulse rise/fall times
- High linearity
- Very low interpulse noise
- Competitively priced

RF Specifications

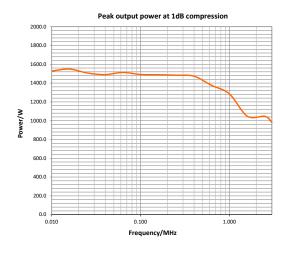
| than approx. 10% of full rated power Pulse droop 0.5dB maximum Measured at max. pulse width at P1dB level Pulse rise and fall times Risetime: 200ns typical Falltime: 100ns typical using a pre-gated RF input signal Gate rise and fall times Risetime: 300ns typical Falltime: 150ns typical Falltime: 150ns typical Falling edge: 1μs typical Falling edge: 500ns typical Rising edge measured from rising edge of GATE pulse to 90% RF output voltage. Falling edge measured from falling edge of GATE pulse to 10% RF output voltage Harmonics Odd: -20dBc typical, -10dBc max. Even: -30dBc typical, -20dBc max. Measured at 1dB below rated output power Spurious -70dBc maximum Output noise (blanked) <10dB above thermal (100kHz bandwidth) Phase change/power Alor from -40dB to full power Phase stability -60dB into 50 Ω (forward voltage sample) Input/output impedance Do Ω nominal Load VSWR Tolerates at least 3:1 @ full rated power without shut down Gain control range OdBm nominal, 10dBm for no damage | KF Specifications | | | |
|---|---------------------------|---|--|--|
| PEP for input power of 0dBm 800W minimum Minimum output power at P1dB compression 6ain 60dB minimum Frequency 0.01MHz-3MHz 6ain flatness ±1.5dB maximum (measured at 1/10th rated output power) Max. duty cycle 20% Maximum GATE duty cycle Max. pulse width 10ms Maximum GATE pulse width Rated power in CW mode 100W CW operation is automatically available at output power level less than approx. 10% of full rated power Pulse droop 0.5dB maximum Measured at max. pulse width at P1dB level Pulse rise and fall times Risetime: 200ns typical Falltime: 100ns typical using a pre-gated RF input signal Gate rise and fall times Risetime: 300ns typical Falltime: 150ns typica | Туре | Class AB MOSFET | | |
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| Control via parallel interface RF Input OdBm nominal, 10dBm for no damage | Load VSWR | Tolerates at least 3:1 @ full rated power without shut down | | |
| | Gain control range | | | |
| GATE (blanking) Logic low = Blank, logic high = unblank. CMOS and TTL compatible | RF Input | 0dBm nominal, 10dBm for no damage | | |
| | GATE (blanking) | Logic low = Blank, logic high = unblank. CMOS and TTL compatible | | |

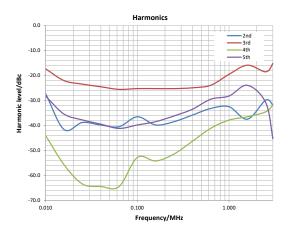
Electrical Specifications

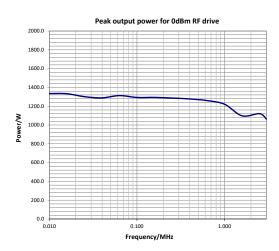
| Mains supply voltage 110-240V, 50-60Hz, single phase | |
|---|--------------|
| Rated Power | 1kVA maximum |
| Mains inlet 1 x IEC inlet (mains power cord supplied) | |

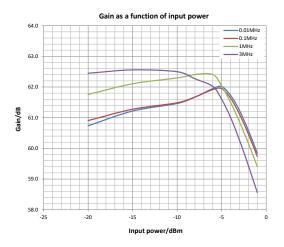


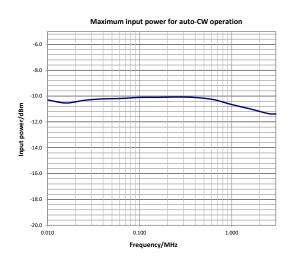
Typical Performance Plots

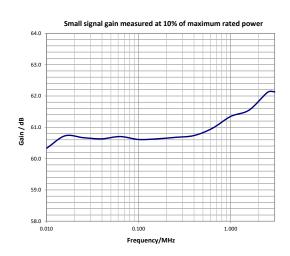










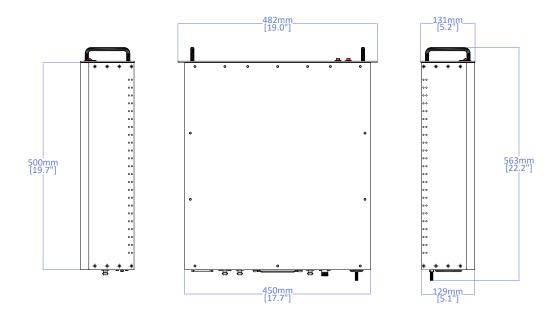


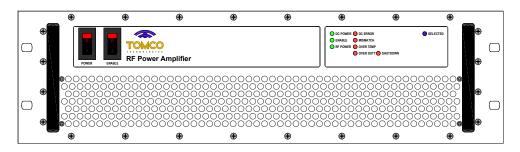
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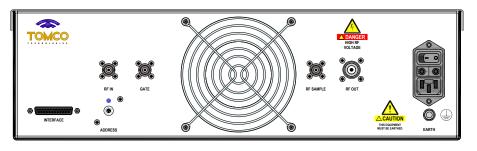


Mechanical Specifications

| Connectors | RF IN: BNC female GATE: BNC female RF SAMPLE: BNC female RF OUT: N type female INTERFACE: DB25 female Other connectors types available on request | | |
|--------------------------|---|--|--|
| Dimensions | Chassis size: 450mmW (17.7"W) x 500mmD (19.7"D) x 129mmH (5.1"H) Total size: 482mmW (19"W) x 563mm (22.2"D) x 131mm (5.2"H) Rack compatibility: 19" 3RU | | |
| Weight | approx. 17kg (38lbs) | | |
| Enclosure classification | IP20 | | |







RF Amplifier Data Sheet

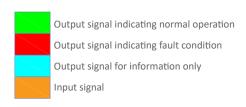


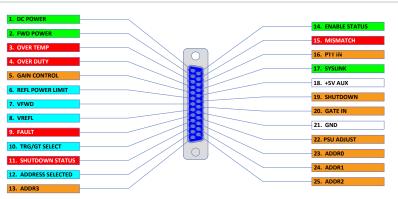
Protection

| Load VSWR | Tolerates up to VSWR 3:1 at full rated power without shutdown Self-resetting shutdown protection activates if VSWR limits are exceeded | | |
|------------------|---|--|--|
| Over temperature | Self-resetting shutdown protection activates if thermal limits are exceeded | | |
| Duty cycle | Duty cycle limit is determined from the GATE signal duty cycle. Self-resetting shutdown protection activates if duty cycle limit is exceeded If output power is less than approx. 10% of maximum rated power, duty cycle protection is disabled and auto-CW operation is available | | |
| Pulse width | Pulse width limit is determined from the GATE signal pulse width. Self-resetting shutdown protection activates if pulse width limit is exceeded | | |

Monitoring and Control

| Front panel switches | Power (turns on DC power) Enable (enables RF) | | |
|----------------------|--|--|--|
| Front panel LEDs | DC POWER DC ERROR SELECTED ENABLE MISMATCH SHUTDOWN RF POWER OVER TEMP OVER DUTY | | |
| Parallel interface | 25-pin D-connector (pinout available at www.tomcorf.com/pdf/interface.pdf)* | | |





Environmental

 $\hbox{*Some functions may be unavailable on select amplifier models}\\$

| General | Intended for use only in controlled, indoor environment. Non-consumer product for industrial and scientific use. This product is not authorised for stand-alone on-air use. Additional systems, hardware and considerations are required to meet local spectral management regulations. Compliance of the final complete system is the responsibility of the end user. | | |
|--------------------------------|--|--|--|
| Cooling | Forced air, front to rear | | |
| Operating temperature | +5°C to +40°C | | |
| Storage temperature | -20°C to +60°C | | |
| Humidity | 80% for temperature up to 31°C, decreasing linearly to 50% relative humidity at 40°C | | |
| Operating altitude | Up to 2000m | | |
| Pollution degree | 2 | | |
| Transient voltage compatibilty | Category II, in line with IEC 60364-4-44:2007 | | |
| Electromagnetic compatibility | In line with IEC61326-1:2012 ISM equipment, Group 1, Class A For use only in shielded areas. ENC55011 (CISPR 11) limits exceeded by up to 50dB | | |
| Safety | In line with IEC61010-1:2010 | | |
| Electromagnetic field strength | In line with ICNIRP Guidelines: 1998, occupational limits | | |

Change record

| Document/Issue number | Originator | Date | Change |
|-----------------------|------------|------------|----------|
| DS006663A | JR | 11/07/2018 | Original |
| DS006663B | JR | 24/07/2019 | p.4:EM |
| DS006663C | LS | 8/04/2020 | p.4:E |
| DS006663D | DW | 10/09/2020 | p.1:RFS |
| DS006663E | LS | 12/01/2021 | p.1:H |
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